

MGBR10S45C

Preliminary

DIODE

DUAL MOS GATED BARRIER RECTIFIER

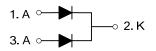
DESCRIPTION

The UTC **MGBR10S45C** is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

FEATURES

* Super low forward voltage drop * High switching speed





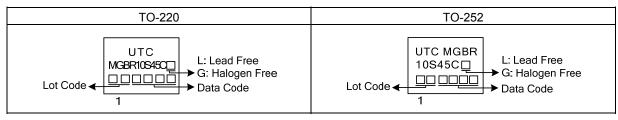
ORDERING INFORMATION

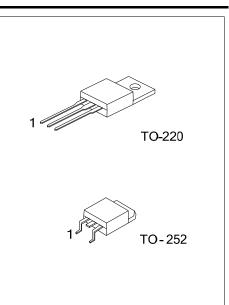
Ordering Number		Deekege	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR10S45CL-TA3-T	MGBR10S45CG-TA3-T	TO-220	Α	К	Α	Tube	
MGBR10S45CL-TN3-R	MGBR10S45CG-TN3-R	TO-252	Α	К	Α	Tape Reel	

Note:	Pin Assignment: A: Anode	K: Common Cathode

(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TN3: TO-252
(3) L: Lead Free, G: Halogen Free and Lead Free

MARKING





Preliminary

■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current b	y 20 /0.			
PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage		V _{RM}	45	V
Working Peak Reverse Voltage		V _{RWM}	45	V
Peak Repetitive Reverse Voltage		V _{RRM}	45	V
RMS Reverse Voltage		V _{R(RMS)}	32	V
Average Rectified Output Current	Per Leg		5	А
(T _C =140°C)	Total	Io	10	А
Non-Repetitive Peak Forward Surge C Single Half Sine-Wave Superimposed		I _{FSM}	100	A
Repetitive Peak Avalanche Power (1µs, 25°C)		P _{ARM}	5000	W
Operating Junction Temperature		TJ	-65~+150	°C
Storage Temperature		T _{STG}	-65~+150	°C
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Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220	0	62.5	°C/W	
	TO-252	θ _{JA}	110		
Junction to Case	TO-220	0	2	°C () ()	
	TO-252	θ _{JC}	2.5	°C/W	

■ ELECTRICAL CHARACTERISTICS (Per Leg) (T_A=25°C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	V _{(BR)R}	I _R =0.45mA	45			V
Forward Voltage Drop	V _{FM}	I _F =5A, T _J =25°C			0.45	V
		I _F =5A, T _J =125°C			0.40	V
Lashana Qumant (Nata 1)	RM	V _R =45V, T _J =25°C		50	500	μA
Leakage Current (Note 1)		V _R =45V, T _J =125°C		12	40	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

2. Thermal resistance junction to case mounted on heatsink.



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